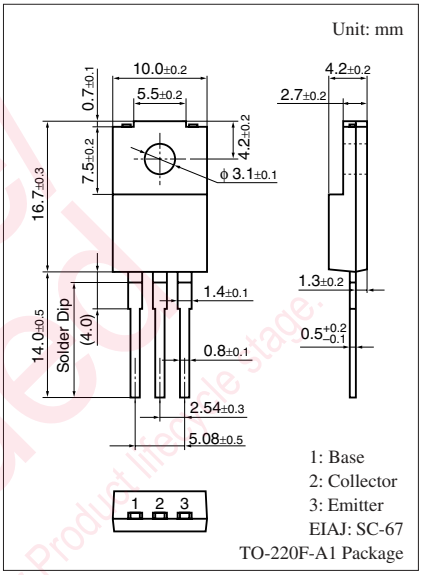
2SB0951 (2SB951), 2SB0951A (2SB951A)

Silicon PNP epitaxial planar type darlington

For midium-speed switching
Complementary to 2SD1277 and 2SD1277A

■ Features

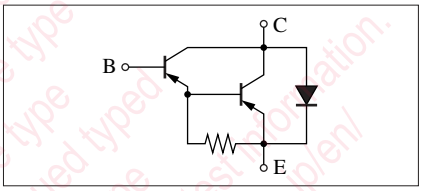
- High forward current transfer ratio h_{FE}
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw



■ Absolute Maximum Ratings $T_C = 25°C$

Parameter		Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SB0951	V_{CBO}	−60	V
	2SB0951A		−80	
Collector-emitter voltage (Base open)	2SB0951	V_{CEO}	−60	V
	2SB0951A		−80	
Emitter-base voltage (Collector open)		V_{EBO}	−7	V
Collector current		I_C	−8	A
Peak collector current		I_{CP}	−12	A
Collector power dissipation		P_C	45	W
	$T_a = 25°C$		2	
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	−55 to +150	°C

Internal Connection



■ Electrical Characteristics $T_C = 25°C \pm 3°C$

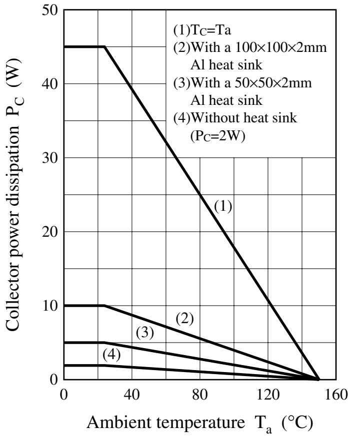
Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SB0951	V_{CEO}	$I_C = -30$ mA, $I_B = 0$	−60			V
	2SB0951A			−80			
Collector-base cutoff current (Emitter open)	2SB0951	I_{CBO}	$V_{CB} = -60$ V, $I_E = 0$			−100	μA
	2SB0951A		$V_{CB} = -80$ V, $I_E = 0$			−100	
Emitter-base cutoff current (Collector open)		I_{EBO}	$V_{EB} = -7$ V, $I_C = 0$			−2	mA
Forward current transfer ratio		h_{FE1} *	$V_{CE} = -3$ V, $I_C = -4$ A	1000		10000	—
		h_{FE2}	$V_{CE} = -3$ V, $I_C = -8$ A	500			
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = -4$ A, $I_B = -8$ mA			−1.5	V
Base-emitter saturation voltage		$V_{BE(sat)}$	$I_C = -4$ A, $I_B = -8$ mA			−2.0	V
Transition frequency		f_T	$V_{CE} = -10$ V, $I_C = -1$ A, f = 1 MHz		20		MHz
Turn-on time		t_{on}	$I_C = -4$ A, $I_{B1} = -8$ mA, $I_{B2} = 8$ mA		0.5		μs
Storage time		t_{stg}	$V_{CC} = -50$ V		2.0		μs
Fall time		t_f			1.0		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. *: Rank classification

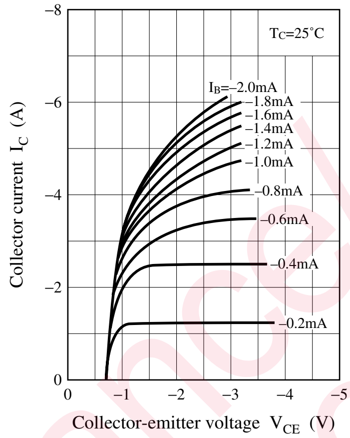
Rank	R	Q	P
h_{FE1}	1000 to 2500	2000 to 5000	4000 to 10000

Note) The part numbers in the parenthesis show conventional part number.

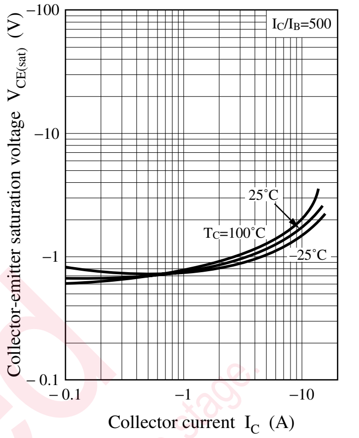
P_C — T_a



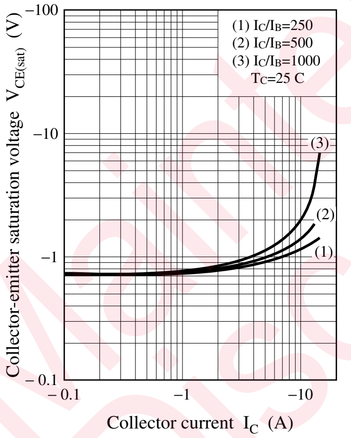
I_C — V_{CE}



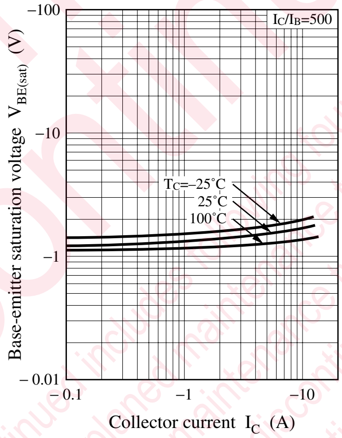
$V_{CE(sat)}$ — I_C



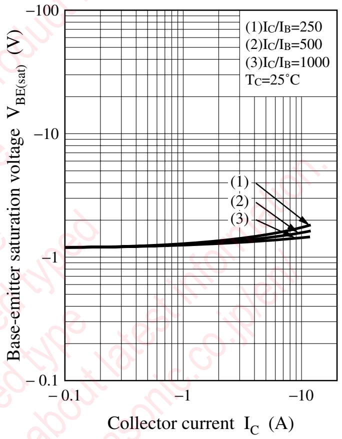
$V_{CE(sat)}$ — I_C



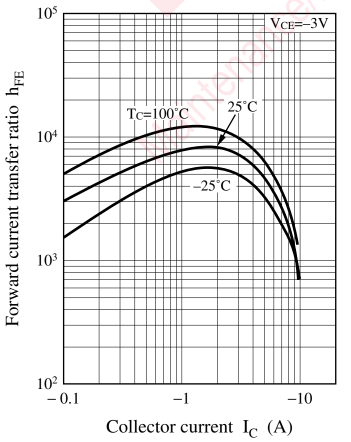
$V_{BE(sat)}$ — I_C



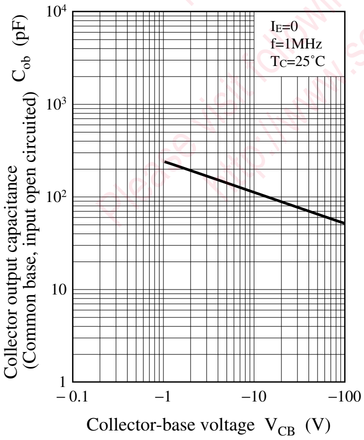
$V_{BE(sat)}$ — I_C



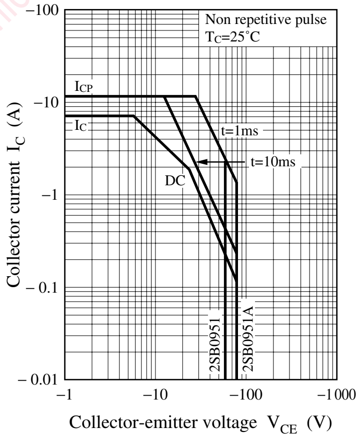
h_{FE} — I_C

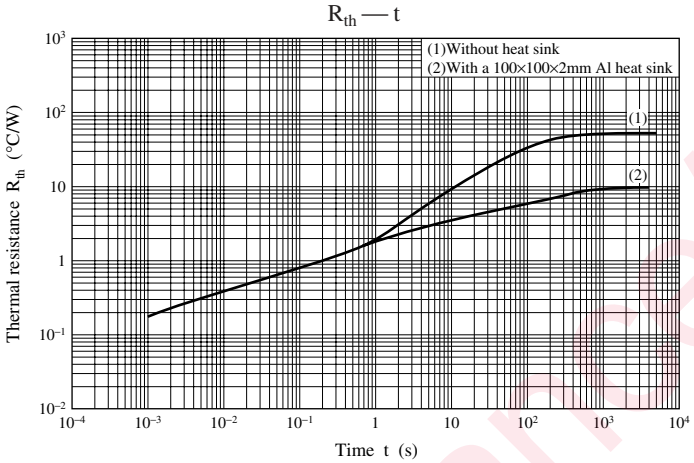


C_{ob} — V_{CB}



Safe operation area





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